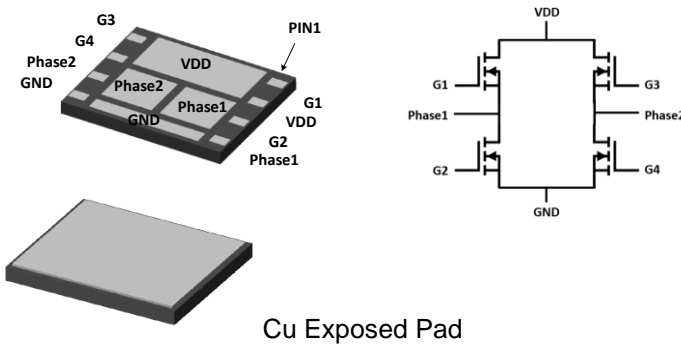


General Description

These N-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.

DFN5X6 4 IN 1 Pin Configuration



BVDSS	RDSON	ID
30V	16mΩ	25A

Features

- 30V,25A, $R_{DS(ON)} = 16m\Omega$ @VGS = 10V
- Improved dv/dt capability
- Fast switching
- 100% EAS Guaranteed
- Green Device Available

Applications

- Full Bridge Applications

Absolute Maximum Ratings $T_c=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current – Continuous ($T_c=25^\circ\text{C}$)	25	A
	Drain Current – Continuous ($T_c=100^\circ\text{C}$)	15.8	A
I_{DM}	Drain Current – Pulsed ¹	100	A
EAS	Single Pulse Avalanche Energy ²	18	mJ
IAS	Single Pulse Avalanched Current ²	19	A
P_D	Power Dissipation ($T_c=25^\circ\text{C}$)	16.9	W
	Power Dissipation – Derate above 25°C	0.14	W/ $^\circ\text{C}$
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to ambient	---	62	$^\circ\text{C}/\text{W}$
$R_{\theta JC}$	Thermal Resistance Junction to Case	---	7.4	$^\circ\text{C}/\text{W}$

Electrical Characteristics (T_J=25 °C, unless otherwise noted)
Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	30	---	---	V
ΔBV _{DSS} /ΔT _J	BV _{DSS} Temperature Coefficient	Reference to 25°C, I _D =1mA	---	0.04	---	V/°C
I _{DSS}	Drain-Source Leakage Current	V _{DS} =30V, V _{GS} =0V, T _J =25°C	---	---	1	uA
		V _{DS} =24V, V _{GS} =0V, T _J =125°C	---	---	10	uA
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA

On Characteristics

R _{DS(ON)}	Static Drain-Source On-Resistance ³	V _{GS} =10V, I _D =6A	---	12.8	16	mΩ
		V _{GS} =4.5V, I _D =5A	---	17.6	23	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	1.2	1.6	2.5	V
ΔV _{GS(th)}	V _{GS(th)} Temperature Coefficient		---	-4	---	mV/°C
g _{fs}	Forward Transconductance	V _{DS} =10V, I _D =6A	---	8	---	S

Dynamic and switching Characteristics

Q _g	Total Gate Charge ^{3, 4}	V _{DS} =15V, V _{GS} =10V, I _D =10A	---	5.2	10	nC
Q _{gs}	Gate-Source Charge ^{3, 4}		---	0.6	1.2	
Q _{gd}	Gate-Drain Charge ^{3, 4}		---	2	4	
T _{d(on)}	Turn-On Delay Time ^{3, 4}	V _{DD} =15V, V _{GS} =10V, R _G =6Ω I _D =1A	---	2.8	5	ns
T _r	Rise Time ^{3, 4}		---	7.2	14	
T _{d(off)}	Turn-Off Delay Time ^{3, 4}		---	15.8	30	
T _f	Fall Time ^{3, 4}		---	4.6	9	
C _{iss}	Input Capacitance	V _{DS} =25V, V _{GS} =0V, F=1MHz	---	370	740	pF
C _{oss}	Output Capacitance		---	70	140	
C _{rss}	Reverse Transfer Capacitance		---	50	100	
R _g	Gate resistance		V _{GS} =0V, V _{DS} =0V, F=1MHz	---	2.2	

Drain-Source Diode Characteristics and Maximum Ratings

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current	V _G =V _D =0V, Force Current	---	---	25	A
I _{SM}	Pulsed Source Current ³		---	---	50	A
V _{SD}	Diode Forward Voltage ³	V _{GS} =0V, I _S =1A, T _J =25°C	---	---	1	V
t _{rr}	Reverse Recovery Time	V _{GS} =0V, I _S =10A, di/dt=100A/μs	---	---	---	nS
Q _{rr}	Reverse Recovery Charge	T _J =25°C	---	---	---	nC

Note :

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. V_{DD}=25V, V_{GS}=10V, L=1mH, I_{AS}=19A., R_G=25Ω, Starting T_J=25°C.
3. The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%.
4. Essentially independent of operating temperature.

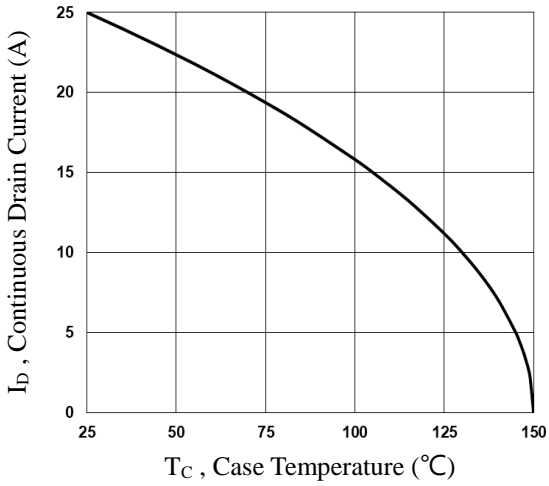


Fig.1 Continuous Drain Current vs. T_c

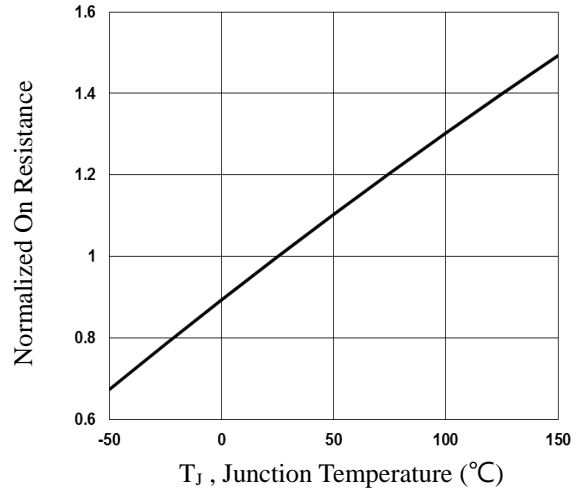


Fig.2 Normalized $R_{DS(on)}$ vs. T_j

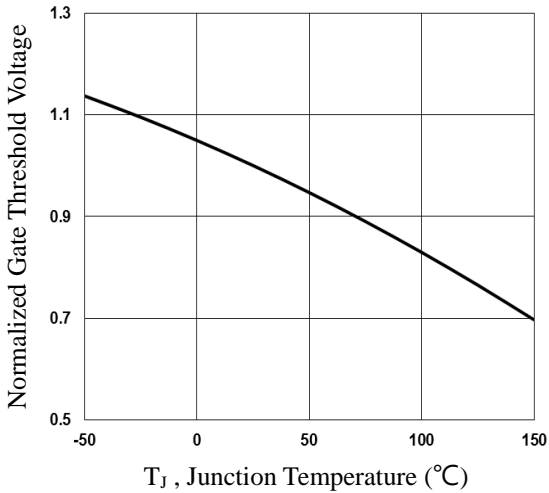


Fig.3 Normalized V_{th} vs. T_j

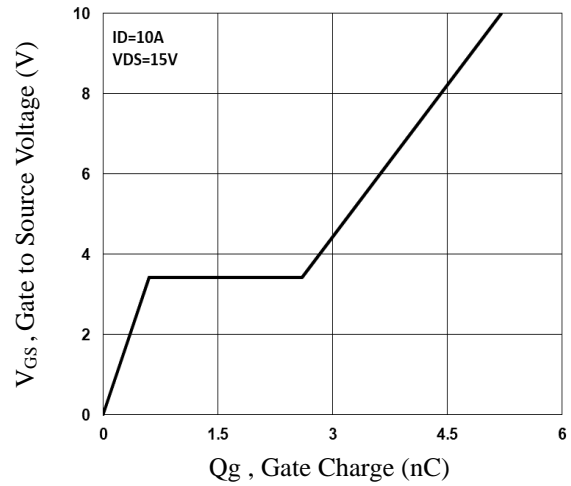


Fig.4 Gate Charge Waveform

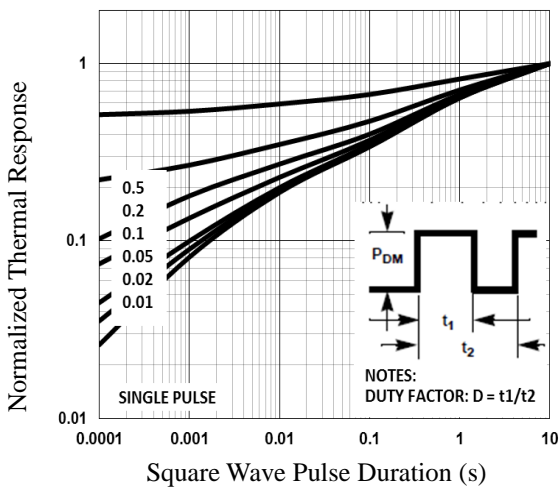


Fig.5 Normalized Transient Response

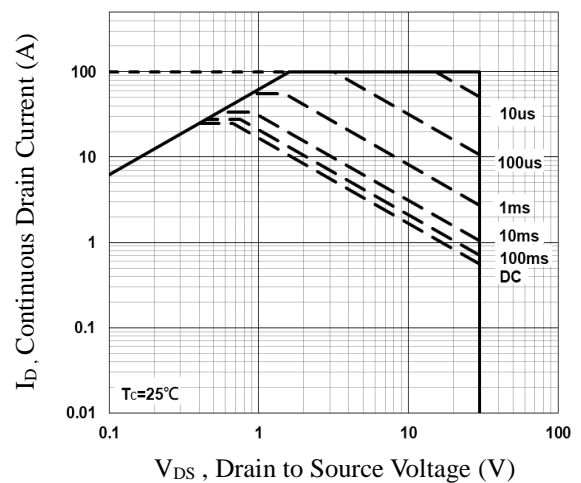


Fig.6 Maximum Safe Operation Area

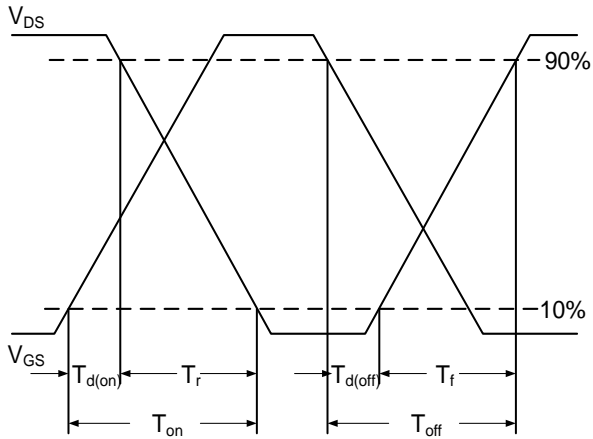


Fig.7 Switching Time Waveform

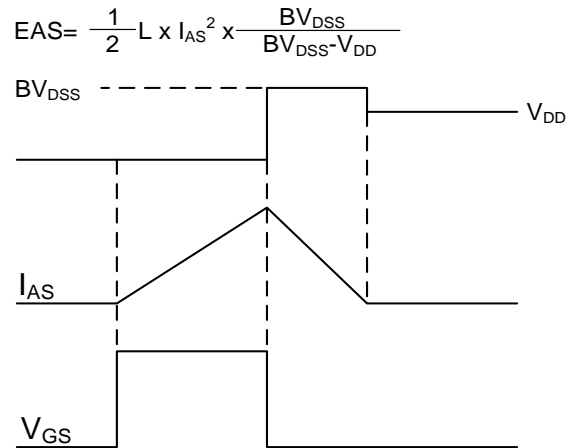
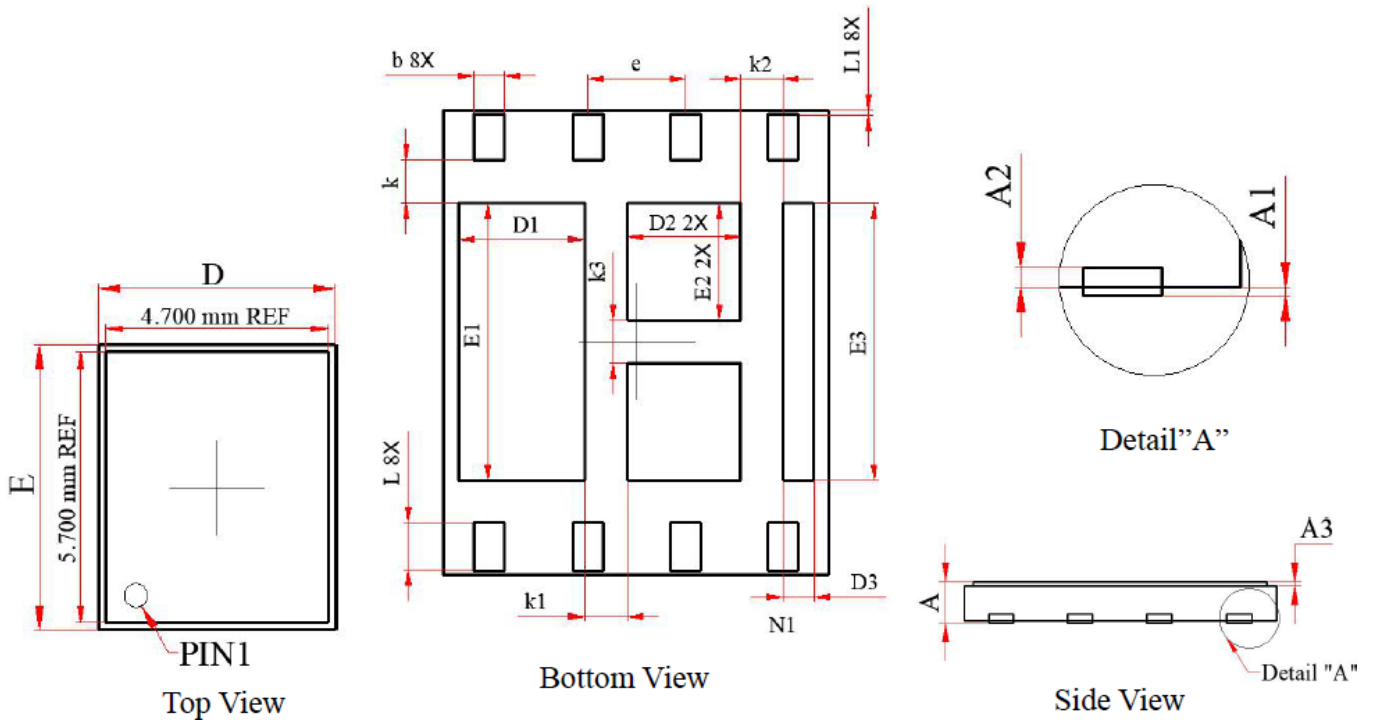


Fig.8 EAS Waveform

DFN5X6 4 IN 1 PACKAGE INFORMATION



Symbol	Dimensions In Millimeters			Symbol	Dimensions In Millimeters		
	MIN	Normal	MAX		MIN	Normal	MAX
A	0.530	---	0.600	D3	0.300	0.400	0.500
A1	---	---	0.005	E3	3.500	3.600	3.700
A2	0.030	---	0.100	b	0.350	0.400	0.450
A3	0.050	---	0.100	L	0.550	0.600	0.650
D	4.900	5.000	5.100	L1	0.010	0.050	0.090
E	5.900	6.000	6.100	k	0.550 REF		
D1	1.525	1.625	1.725	k1	0.550 REF		
E1	3.500	3.600	3.700	k2	0.550 REF		
D2	1.375	1.475	1.575	k3	0.550 REF		
E2	1.425	1.525	1.625	e	1.27 BSC		

DFN5X6 4 IN 1 RECOMMENDED FOOTPRINT

